

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF TAKASHI HAGINO ET AL.

FOR: METHOD FOR MANUFACTURING POLYCRYSTALLINE SEMICONDUCTOR
LAYERS AND THIN-FILM TRANSISTORS, AND LASER ANNEALING
APPARATUS

#5/A
2-6-03
Jun

AMENDMENT

Commissioner of Patents and Trademarks
Washington, DC 20231

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D.C. 20231.
NIDIA M. DEBAS
(Typed or printed name of person mailing paper or fee)
Nida M. Debas
(Signature of person mailing paper or fee)

Dear Sir:

Before examining the present application, please amend as follows:

IN THE TITLE:

Please amend the title in "clean" format, as follows:

METHOD FOR MANUFACTURING POLYCRYSTALLINE
SEMICONDUCTOR LAYERS AND THIN-FILM TRANSISTORS,
AND LASER ANNEALING APPARATUS

IN THE SPECIFICATION:

Please amend the paragraph beginning on page 2, line 21 and continuing to page 3, line 8 in
"clean" format, as follows:

The process atmosphere in the chamber during annealing is one important factor
influencing the surface roughness and crystallizability of a p-Si. Excimer laser annealing in a
nitrogen atmosphere under normal pressure can realize a high productivity of a polycrystalline
silicon film. However, research of the present applicant demonstrated that it is difficult to
control the surface roughness of a p-Si manufactured in the nitrogen atmosphere under the